

# Calculated influences of starting materials composition on carbothermal nitridation synthesis of silicon nitride/silicon carbide composite powders

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Equilibrium phase composition at 1 atm total pressure is quantitatively calculated as the function of starting materials composition for carbothermal nitridation synthesis of Si<sub>3</sub>N<sub>4</sub>/SiC composite powders. N<sub>2</sub> flow is simulated by the N<sub>2</sub> amount in the starting materials. At low starting N<sub>2</sub> content (molar ratio N<sub>2</sub>/SiO<sub>2</sub> ≤ 100), Si<sub>3</sub>N<sub>4</sub> and SiC can not exist in equilibrium at the same temperature. At higher starting N<sub>2</sub> content, the Si<sub>3</sub>N<sub>4</sub>-SiC coexisting temperature range appears above 1760 K. The upper limit of the temperature range becomes higher with increasing starting N<sub>2</sub> content. Starting carbon content affects the composition in the equilibrium powder products. The calculation results are compared with experiments. © 2001 Kluwer Academic Publishers

## 1. Introduction

Nanometer-sized silicon carbide (SiC) particles-reinforced silicon nitride (Si<sub>3</sub>N<sub>4</sub>) matrix composite (Si<sub>3</sub>N<sub>4</sub>/SiC nanocomposite) was found to have substantial increase in mechanical properties over the Si<sub>3</sub>N<sub>4</sub> monolithic material at both room and elevated temperatures [1, 2]. A considerable amount of researches have focused on fabrication methods to make Si<sub>3</sub>N<sub>4</sub>/SiC nanocomposite powders. One such research involved mixing micron/submicron Si<sub>3</sub>N<sub>4</sub> and nanometer-sized SiC powders through mechanical milling [3]. This approach is simple, but difficult to obtain uniformly distributed SiC particles in the Si<sub>3</sub>N<sub>4</sub> matrix, thus resulting in only a small increase in mechanical properties. Another research used chemical vapor deposition to prepare amorphous Si-N-C powders, which crystallized into Si<sub>3</sub>N<sub>4</sub>/SiC nanocomposites during sintering [4]. This method produced a homogeneous distribution of SiC particles and, consequently, resulted in superior mechanical properties. However, this method requires expensive raw materials. Other approaches include pyrolysis of organic precursors [5], coating carbon on Si<sub>3</sub>N<sub>4</sub> powders by pyrolysis of methane (SiC nanoparticles would form as a result of the reaction between the coated carbon and silica (SiO<sub>2</sub>) located on the surface of Si<sub>3</sub>N<sub>4</sub> particles) [6], and partial reduction of Si<sub>3</sub>N<sub>4</sub> powders by pyrolyzed carbon [7].

Industrial SiC powders are produced extensively by carbothermal reduction of SiO<sub>2</sub> due to its relatively low cost in comparison to other methods [8]. The size of SiC

particles is, to a great extent, determined by the size of carbon particles before reduction [9]. Carbothermal nitridation of SiO<sub>2</sub> used to synthesize Si<sub>3</sub>N<sub>4</sub> powders is also cost-effective [10]. By synthesizing Si<sub>3</sub>N<sub>4</sub> and SiC simultaneously through carbothermal reduction of SiO<sub>2</sub> in the presence of nitrogen, a combination of low cost and uniform distribution of SiC nanoparticles are expected. This method to synthesize Si<sub>3</sub>N<sub>4</sub>/SiC nanocomposite powders has been experimentally investigated and generated the expected results [11].

It is convenient to conduct carbothermal nitridation of SiO<sub>2</sub> in flowing N<sub>2</sub> at 1 atm total pressure. Thermodynamic calculation is helpful for understanding the influences of such important parameters as N<sub>2</sub> flow, carbon content, and temperature. Some work has been done concerning thermodynamics of Si-N-O [12, 13], Si-C-O [13], and Si-C-N-O [14, 15] systems and the phase stability regions have been plotted as the function of temperature and partial pressure of gases. However, the control of partial pressures is difficult to conduct in practice. The gas-phase compositions and the phases in equilibrium with the gases in the Si-C-N-O system were calculated by Weiss *et al.* [16], but the equilibrium phase contents which vary depending on the composition of starting materials and the temperature were not clearly demonstrated. This paper reports the thermodynamic calculation of carbothermal nitridation of SiO<sub>2</sub> for predicting equilibrium phase contents, with starting materials composition and temperature as variables. The Si<sub>3</sub>N<sub>4</sub>-SiC coexisting condition is obtained.

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## 2. Calculation

The calculation is performed using the ZGRG program developed by Zhu [17] for thermodynamic computations of complex systems. The modeling of this program is based on the principle that a closed system is in equilibrium only when its Gibbs free energy reaches the minimum [18]. The Gibbs free energy,  $G$ , of a closed system is formulated as

$$G = \sum_{i=1}^N n_i \mu_i \quad (1)$$

where  $n_i$  and  $\mu_i$  are, respectively, the mole number and chemical potential of species  $i$  in the system, and  $N$  is the number of species. The value of  $n_i$  must satisfy the following two constraints:

$$n_i \geq 0 \quad (i = 1, 2, 3, \dots, N) \quad (2)$$

$$\sum_{i=1}^N a_{ij} n_i = E_j \quad (j = 1, 2, 3, \dots, M) \quad (3)$$

where  $a_{ij}$  is the atom number of element  $j$  in the chemical formula of species  $i$ ,  $E_j$  the mole number of element  $j$ , and  $M$  the number of elements in the system. The equilibrium composition, namely  $n_i^{\text{eq}}$ , is therefore obtained by minimizing  $G$  with the constraints of Equations 2 and 3. This is a nonlinear optimization problem. The ZGRG program uses generalized reduced gradient method (GRG), firstly developed by Lasdon *et al.* [19], as its nonlinear optimizing algorithm.

Due to the lack of sufficient data for activity and fugacity coefficients, some approximations are made. As the temperature under consideration is higher than 1000 K and the total pressure is 1 atm, the ideal gas model is employed, i.e.

$$\mu_i = \mu_i^0 + RT \ln P y_i \quad (4)$$

where  $\mu_i^0$  is the chemical potential of gas  $i$  under standard condition and  $\mu_i^0 = G_i^0$ , where  $G_i^0$  is the standard Gibbs free energy of formation for species  $i$ .  $R$  is the universal gas constant,  $T$  the temperature in Kelvins,  $P$  the total pressure, and  $y_i$  the mole fraction of gas  $i$  in the gaseous phase. No solutions are considered. As for the pure condensed phases,

$$\mu_i = \mu_i^0 = G_i^0 \quad (5)$$

The species considered in the calculation and their standard Gibbs free energies of formation are shown in Table I. Since only a few specific heat data are available, the standard Gibbs free energy is described solely as a linear function of the temperature. The reference states are graphite, liquid silicon, and gaseous  $\text{N}_2$  and  $\text{O}_2$ . The data for C(l) and Si(s) are, respectively, from Weiss *et al.* [16] and Hultgren *et al.* [20], and that for  $\text{Si}_2\text{N}_2\text{O}$ ,  $\alpha\text{-Si}_3\text{N}_4$  and  $\beta\text{-Si}_3\text{N}_4$  are from Hendry [21, 22]. The remaining data are from JANAF tables [23]. According to [15] the chemical formula for  $\alpha\text{-Si}_3\text{N}_4$  is  $\text{Si}_{2.85}\text{N}_{3.75}\text{O}_{0.075}$ .

TABLE I Standard Gibbs free energy of formation ( $G_i^0 = A + BT$ ) in the Si-C-N-O system

Species	A (J/mol)	B (J/mol/K)	Species	A (J/mol)	B (J/mol/K)
<b>Gases</b>					
C	714985.7	-156.75	CO	-119945.9	-83.05
C <sub>2</sub>	829360.1	-188.65	CO <sub>2</sub>	-397189.3	0.268
C <sub>3</sub>	763506.5	-185.1	SiO	-166118.5	-45.27
Si	391083.6	-111.63	SiO <sub>2</sub>	-362659.1	32.02
Si <sub>2</sub>	470398.7	-113.64	NO	90476.6	-12.69
Si <sub>3</sub>	448449.5	-90.449	<b>Liquids</b>		
SiC	657941.0	-154.7	C	14223.6	-27.196
Si <sub>2</sub> C	407283.4	-114.31	Si	0.0	0.0
SiC <sub>2</sub>	544932.9	-162.38	<b>Solids</b>		
N <sub>2</sub>	0.0	0.0	C	0.0	0.0
N	480695.8	-67.01	Si	-50208.0	29.797
CN	428824.9	-97.22	$\beta\text{-SiC}$	-122110.0	36.002
C <sub>2</sub> N <sub>2</sub>	311324.9	-44.69	$\alpha\text{-SiC}$	-120319.2	36.798
SiN	311821.8	-61.15	$\alpha\text{-Si}_3\text{N}_4$	-1317924.0	683.391
Si <sub>2</sub> N	279914.9	-47.52	$\beta\text{-Si}_3\text{N}_4$	-1086624.0	539.391
O <sub>2</sub>	0.0	0.0	SiO <sub>2</sub> (Cr.)	-944893.6	196.91
O	255742.5	-67.01	SiO <sub>2</sub> (Tr.)	-946651.7	197.912
			Si <sub>2</sub> N <sub>2</sub> O	-758716.0	190.594

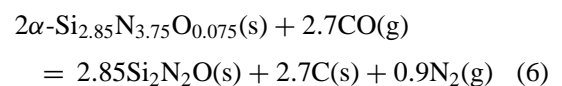
## 3. Results and discussion

### 3.1. Influence of nitrogen flow

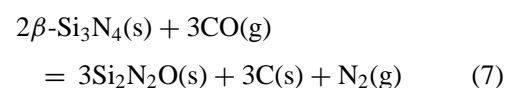
The  $\text{N}_2$  flow is described as the starting  $\text{N}_2$  content (SNC) in the raw materials. With starting  $\text{SiO}_2$  and carbon being 1 mol and 2.5 mol, respectively, and the variation of SNC from 4–4000 mol, the influence of SNC on the equilibrium composition is calculated. The species existing in the equilibrium composition are shown in Fig. 1, with the exception of  $\text{N}_2$  and some species found in a considerable small amount such as SiN(g).

It is clear from Fig. 1 that SNC determines whether  $\text{Si}_3\text{N}_4/\text{SiC}$  composite powder would exist in the equilibrium products after carbothermal nitridation of  $\text{SiO}_2$ . High SNC is necessary to produce  $\text{Si}_3\text{N}_4/\text{SiC}$  composite powders. When  $\text{SNC} \leq 100$  mol,  $\text{Si}_3\text{N}_4$  and SiC can not exist in an equilibrium at the same temperature. By increasing SNC to 200 mol, the  $\text{Si}_3\text{N}_4\text{-SiC}$  coexisting region appears at the temperature between 1670 and 1705 K. The coexisting region widens to 1670–1755 K when SNC is 400 mol, and further widens to 1670–1840 K when SNC is 4000 mol. Thermodynamically  $\text{Si}_3\text{N}_4/\text{SiC}$  composite powders can be synthesized in the  $\text{Si}_3\text{N}_4\text{-SiC}$  coexisting temperature range without other solid contaminants such as  $\text{Si}_2\text{N}_2\text{O}$ .

The appearance of  $\text{Si}_3\text{N}_4\text{-SiC}$  coexisting temperature range is the result of the widening of the  $\text{Si}_3\text{N}_4$  and SiC existing temperature ranges. It is evident that the highest  $\text{Si}_3\text{N}_4$  existing temperature,  $T_{\text{SN}}^{\text{high}}$ , is governed by the reaction



in Fig. 1a and b, by the reaction



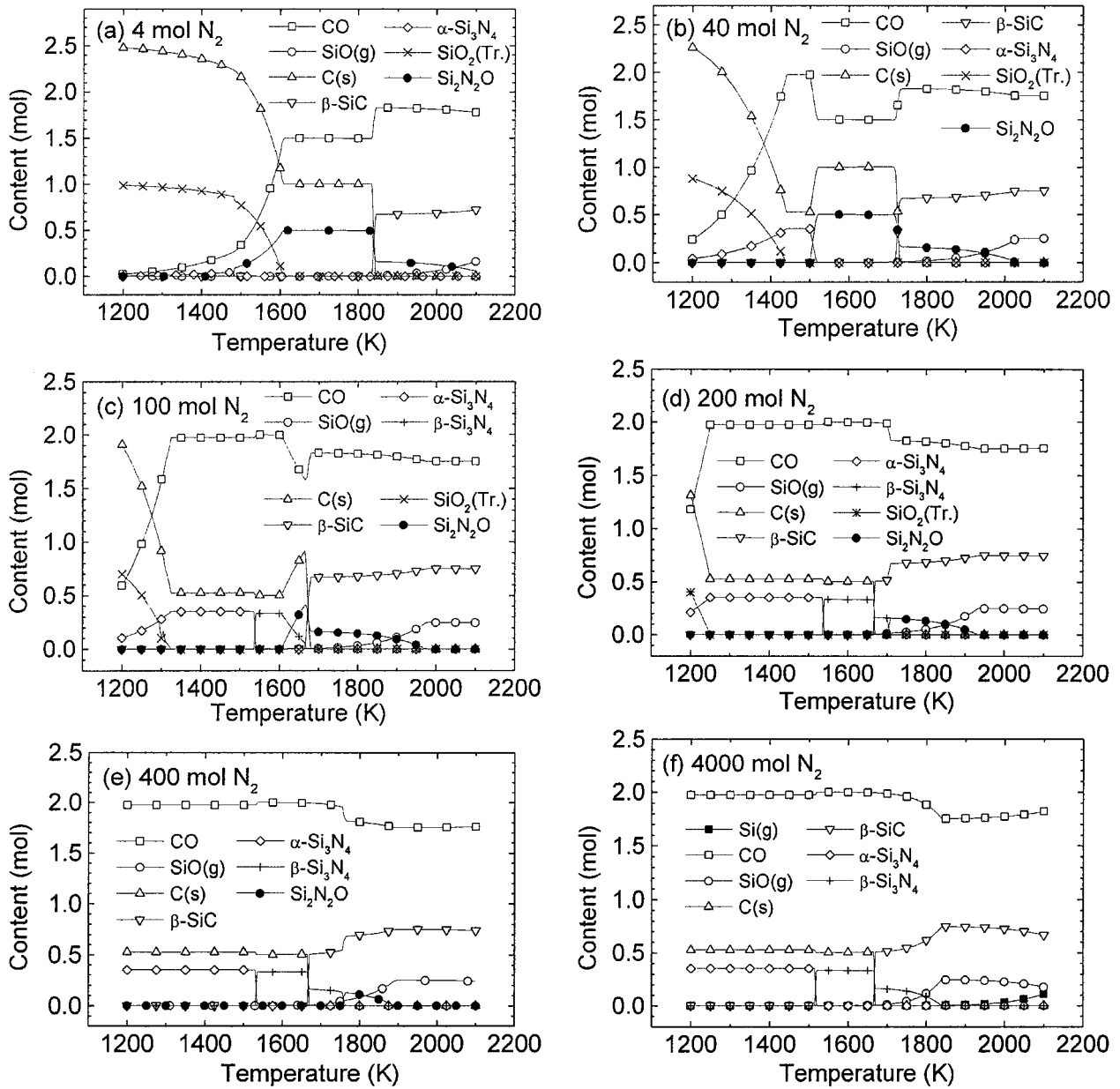
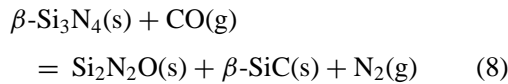
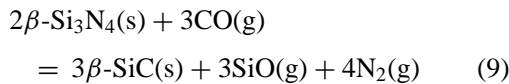


Figure 1 Calculated equilibrium composition of carbothermal nitridation of SiO<sub>2</sub> at 1 atm total pressure, with starting SiO<sub>2</sub> and carbon being 1.0 mol and 2.5 mol, respectively, and starting N<sub>2</sub> being (a) 4 mol, (b) 40 mol, (c) 100 mol, (d) 200 mol, (e) 400 mol, and (f) 4000 mol.

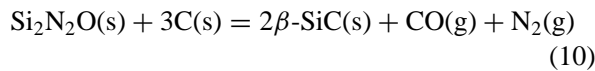
in Fig. 1c, by the reaction



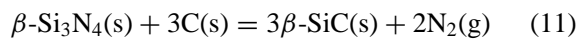
in Fig. 1d and e, and by the reaction



in Fig. 1f. The lowest SiC existing temperature,  $T_{\text{SC}}^{\text{low}}$ , is governed by the reaction



in Fig. 1a–c, and by the reaction

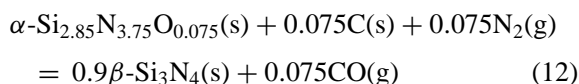


in Fig. 1d, e and f. At low SNC  $T_{\text{SN}}^{\text{high}} < T_{\text{SC}}^{\text{low}}$ . Since the total pressure is 1 atm and the N<sub>2</sub> partial pressure,  $p_{\text{N}_2}$ , is more than 0.5 atm in Fig. 1a, the increase of  $p_{\text{N}_2}$  is limited to less than 0.5 atm when further increasing SNC, while the CO and SiO partial pressures can decrease by several orders. Therefore, with the increase of SNC, Si<sub>3</sub>N<sub>4</sub> will stabilize at a higher temperature according to the reaction (6)–(9), i.e.  $T_{\text{SN}}^{\text{high}}$  becomes higher, and similarly,  $T_{\text{SC}}^{\text{low}}$  becomes lower according to the reaction (10). When  $T_{\text{SN}}^{\text{high}} > T_{\text{SC}}^{\text{low}}$ , the Si<sub>3</sub>N<sub>4</sub>-SiC coexisting region appears.  $T_{\text{SC}}^{\text{low}}$  remains unchanged in Fig. 1d, e and f because at high SNC the variation of SNC has almost no influence on  $p_{\text{N}_2}$ , which determines the balance of the reaction (11).

These results are compared with reported experiments. In the experiments by Carroll *et al.* [11], the flowing N<sub>2</sub> consumed during the reaction is estimated at more than 100 N<sub>2</sub>/SiO<sub>2</sub> molar ratio, and Si<sub>3</sub>N<sub>4</sub>/SiC nanocomposite powders were synthesized

in the temperature range as calculated above. Because  $\beta$ - $\text{Si}_3\text{N}_4$  disappears at 1665 K and  $\beta$ -SiC appears at 1670 K in Fig. 1c, the  $\text{Si}_3\text{N}_4$ -SiC coexisting temperature is expected to appear at a slightly higher SNC. However, this prediction should not be considered quantitatively precise because of the approximations in the calculation and the neglect of kinetic factors. In carbothermal nitridation synthesis of  $\text{Si}_3\text{N}_4$  powders high  $\text{N}_2$  flow is also preferable because the wider  $\text{Si}_3\text{N}_4$  existing temperature range is expected at higher SNC, as shown in Fig. 1. For example, Weimer *et al.* conducted the synthesis with an estimated flowing  $\text{N}_2/\text{SiO}_2$  molar ratio of several hundreds [24].

The  $\alpha \rightarrow \beta$ - $\text{Si}_3\text{N}_4$  transformation temperature is 1540 K in Fig. 1c and d, 1535 K in Fig. 1e, and 1520 K in Fig. 1f, decreasing with the increase of SNC. This is because the transformation occurs according to the gas-involving reaction



Jha [15] predicted that at 1 atm of  $\text{N}_2$  pressure, the  $\alpha$ -phase closed at  $\sim 1500$  K, which is close to that predicted at high SNC in this study.

### 3.2. Influence of starting carbon content

In the above calculation the starting carbon content (SCC) and  $\text{SiO}_2$  are fixed at 2.5 mol and 1.0 mol, respectively. Computation with different starting carbon content results in the same conclusion: that  $\text{Si}_3\text{N}_4/\text{SiC}$  composite powders can only be synthesized at high SNC. The composition of the equilibrium powder product prepared at high SNC varies according to the changing carbon content, which is typically illustrated in Fig. 2. At  $\text{SCC} < 2.0$  mol, no SiC exists in the powder; at  $\text{SCC} > 3.0$  mol, no  $\text{Si}_3\text{N}_4$  exists. At  $\text{SCC} = 2.0\text{--}3.0$  mol,  $\text{Si}_3\text{N}_4/\text{SiC}$  composite powders are thermodynamically produced, with  $\text{Si}_3\text{N}_4$  and SiC contents changing linearly according to the variation of SCC.

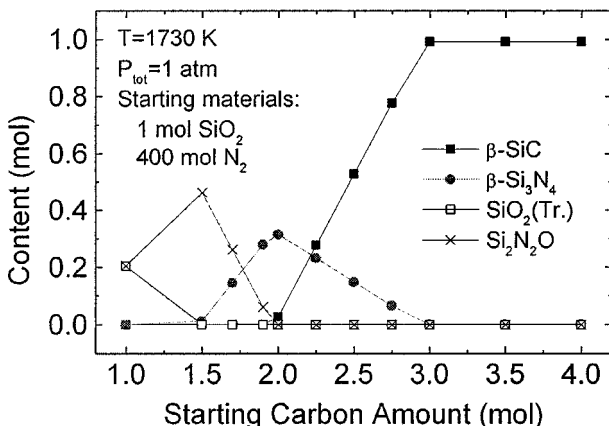


Figure 2 The composition of equilibrium composite powder product as the function of starting carbon content.

As two solid reactants, namely carbon and  $\text{SiO}_2$ , are involved in carbothermal nitridation reaction, the mixing condition of these two starting materials greatly influences the reaction kinetics. Due to the difficulty in obtaining a homogeneous mixture of the starting materials, the amount of carbon effective in the reaction is less than that contained in the mixture. Therefore, in practice, the amount of carbon should exceed the theoretical requirement in the synthesis of  $\text{Si}_3\text{N}_4/\text{SiC}$  composite powders, as in the work by Carroll *et al.* [11].

### 4. Conclusions

In the carbothermal nitridation of  $\text{SiO}_2$  at 1 atm total pressure,  $\text{Si}_3\text{N}_4/\text{SiC}$  composite powders can only be synthesized at a high starting  $\text{N}_2$  content ( $\text{N}_2$  flow). In equilibrium there is no  $\text{Si}_3\text{N}_4$ -SiC coexisting temperature range at the molar ratio of  $\text{N}_2/\text{SiO}_2 \leq 100$ , while at higher  $\text{N}_2/\text{SiO}_2$  ratio the coexisting temperature range appears. Starting carbon amount influences  $\text{Si}_3\text{N}_4$  and SiC contents in the powder products.

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